

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE WITH CONTACT
BODY EXTENDING IN DIRECTION OF BIT LINE TO CONTACT STORAGE NODE

ABSTRACT OF THE DISCLOSURE

5 A method of manufacturing a semiconductor device with contact bodies that extend in
the direction of bit lines to contact storage nodes includes forming band-type openings by
selectively etching an insulating layer that covers the bit lines. The band-type openings
extend in a lengthwise direction of the gate lines to expose the first contact pads and have
portions that protrude in a lengthwise direction of the bit lines. The method also includes
10 forming a conductive layer on the insulating layer that fills the band-type openings and is
electrically connected to the first contact pads. The conductive layer is then patterned to
separate the conductive layer into individual storage node contact bodies that extend in a
lengthwise direction of the bit lines. Storage nodes are then formed on the storage node
contact bodies.

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